# DOCUMENT CHANGE REQUEST

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|---|---|---|
| DCR number 1093 | Changes required for: General | Originator: Samuel Savin |
| Date: 2024/02/29 | Date sent: 2017/06/06 | Organisation: STMicroelectronics |
| Status: IMPLEMENTED | | |

| | | | |
|---|---|---|---|
| Title: | Diodes Switching, based on types 1N5807 through 1N5811 | | |
| Number: | 5101/013 | Issue: | 6 |

Other documents affected:

5101/014-6, 5101/026-6, 5101/027-5

Page:

Paragraph:

Appendix A

Original wording:

1- For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 7050651.

2- All AC characteristics (C, xx, xx) may be considered guaranteed but not tested if successful pilot lot testing has been performed in accordance with STMicroelectronics procedure 7188211 on the wafer lot, which includes AC characteristic measurements per the Detail Specification

Proposed wording:

1- For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics control plans internal procedure, as specified in the PID

2- All AC characteristics (C, xx, xx) may be considered guaranteed but not tested if successful pilot lot testing has been performed in accordance with STMicroelectronics wafers acceptation internal procedure, as specified in the PID, which includes AC characteristic measurements per the Detail Specification

Justification:

just added the reference to the approved PID

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| Status: IMPLEMENTED | | |

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| Title: | Diodes Switching, based on types 1N5807 through 1N5811 | | |
| Number: | 5101/013 | Issue: | 6 |

**Other documents affected:**

5101/014-6, 5101/026-6, 5101/027-5, 5106/020-5, 5106/021-5

**Page:**

**Paragraph:**

APPENDIX ‘A’

**Original wording:**

1- For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 7050651.

2- All AC characteristics (C, xx, xx) may be considered guaranteed but not tested if successful pilot lot testing has been performed in accordance with STMicroelectronics procedure 7188211 on the wafer lot, which includes AC characteristic measurements per the Detail Specification.

**Proposed wording:**

1- For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics control plans internal procedure.

2- All AC characteristics (C, xx, xx) may be considered guaranteed but not tested if successful pilot lot testing has been performed in accordance with STMicroelectronics wafers acceptation internal procedure, which includes AC characteristic measurements per the Detail Specification.

**Justification:**

1- Procedure 7050651 corresponded to the internal procedure “CONTROL PLAN ASSEMBLY”. This procedure has been replaced by the procedure DMS 8384044 “CONTROL PLANS BACK END RENNES” gathering all the hirel ST control plans.

2- Procedure 7188211 corresponded to the internal procedure for the diode pilot lots. This procedure has been replaced by the generic procedure DMS 00111752 gathering all the hirel ST products with the French title  Acceptation wafers pour utilisation haute fiabilité: Lots Pilotes .

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| DCR number 1093 | Changes required for: General | Originator: Samuel Savin |
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| Date: 2024/02/29 | Date sent: 2017/06/06 | Organisation: STMicroelectronics |
| Status: IMPLEMENTED | | |

| Title: | Diode, Silicon, Power Schottky Rectifier, based on Type 1N5819 | | |
|---|---|---|---|
| Number: | 5106/021 | Issue: | 5 |

Other documents affected:

Page:

Paragraph:

Appendix A

Original wording:

1- For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 7050651.

2- All AC characteristics (C, xx, xx) may be considered guaranteed but not tested if successful pilot lot testing has been performed in accordance with STMicroelectronics procedure 7188211 on the wafer lot, which includes AC characteristic measurements per the Detail Specification.

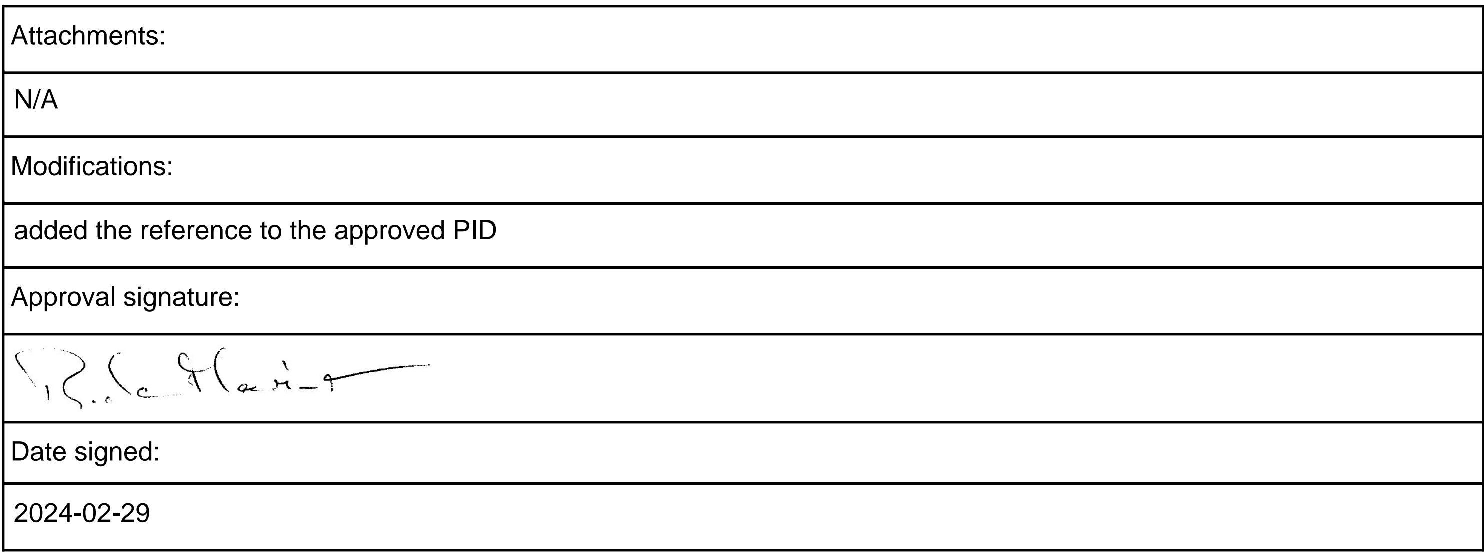
Proposed wording:

1- For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics control plans internal procedure, as specified in the PID.

2- All AC characteristics (C, xx, xx) may be considered guaranteed but not tested if successful pilot lot testing has been performed in accordance with STMicroelectronics wafers acceptation internal procedure, as specified in the PID, which includes AC characteristic measurements per the Detail Specification.

Justification:

just added the reference to the PID



| Attachments: |
| --- |
| N/A |
| Modifications: |
| added the reference to the approved PID |
| Approval signature: |
| |
| Date signed: |
| 2024-02-29 |